

# FH3415Q

## P-Channel Enhancement Mode MOSFET

### Description

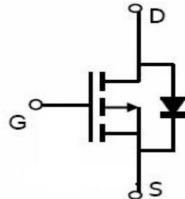
- ◆ Trench Power LV MOSFET technology
- ◆ High Power and Current handing capability
- ◆ Low Gate Charge

### Application

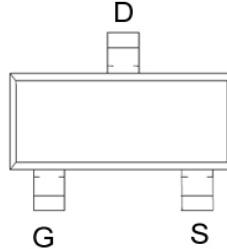
- ◆ PWM applications
- ◆ Power management
- ◆ Load switch

### General Features

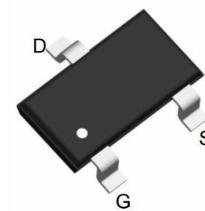
- ◆  $V_{DS} = -20V$ ;  $I_D = -3.0A$
- ◆  $R_{DS(ON)}(\text{Typ.}) = 45\text{ m}\Omega$  @  $V_{GS} = -10V$
- ◆  $R_{DS(ON)}(\text{Typ.}) = 65\text{ m}\Omega$  @  $V_{GS} = -4.5V$
- ◆  $R_{DS(ON)}(\text{Typ.}) = 55\text{ m}\Omega$  @  $V_{GS} = -5.0V$
- ◆ LogicLevelCompatible
- ◆ SMD Package(SOT-23)
- ◆ TrenchTechnology
- ◆ FastSwitching



Schematic diagram



Marking and Pin Assignment



SOT-23 top view

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	$V_{DS}$	-20	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current <small><math>T_A=25^\circ\text{C}</math></small>	$I_D$	-3.0	A
		-2.4	
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	-12.0	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	$P_D$	1	W
Thermal Resistance Junction-to-Ambient <sup>B</sup>	$R_{\theta JA}$	139	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 ~ +150	$^\circ\text{C}$

**Electrical Characteristics** (TA=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =-250μA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V, T <sub>C</sub> =25°C			-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.3	-1.6	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -5.0V, I <sub>D</sub> =-1A		55	70	mΩ
		V <sub>GS</sub> = -10V, I <sub>D</sub> =-3.0A		45	64	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-2.0A		65	83	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3.0A, V <sub>GS</sub> =0V		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-3.4	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHZ		470		pF
Output Capacitance	C <sub>oss</sub>			68		
Reverse Transfer Capacitance	C <sub>rss</sub>			42		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, I <sub>D</sub> =-3.0A		3.8		nC
Gate Source Charge	Q <sub>gs</sub>			0.8		
Gate Drain Charge	Q <sub>gd</sub>			1.1		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =-4.5V, V <sub>DD</sub> =-10V, I <sub>D</sub> =-1A, R <sub>GEN</sub> =2.5Ω		12		ns
Turn-on Rise Time	t <sub>r</sub>			52		
Turn-off Delay Time	t <sub>D(off)</sub>			14		
Turn-off Fall Time	t <sub>f</sub>			9		

- A. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.  
 B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

## Typical Performance Characteristics

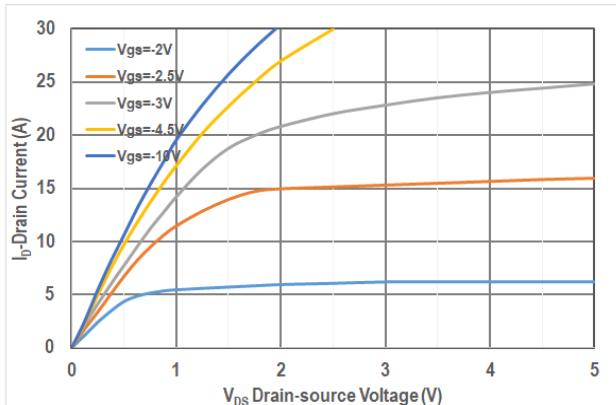


Figure1. Output Characteristics

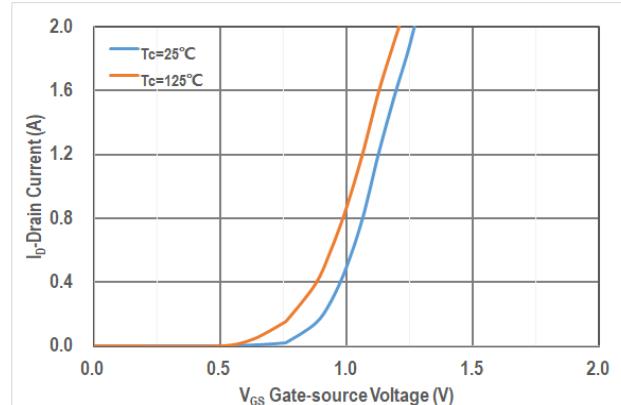


Figure2. Transfer Characteristics

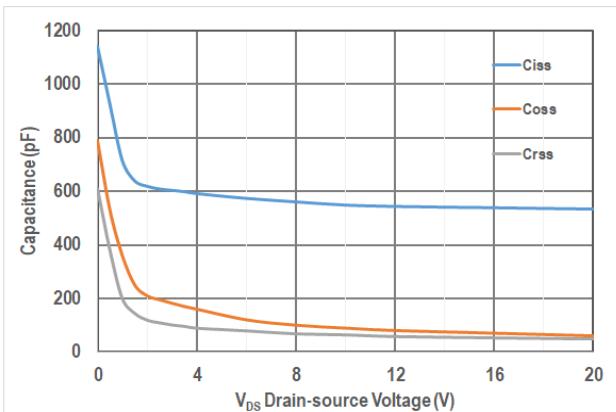


Figure3. Capacitance Characteristics

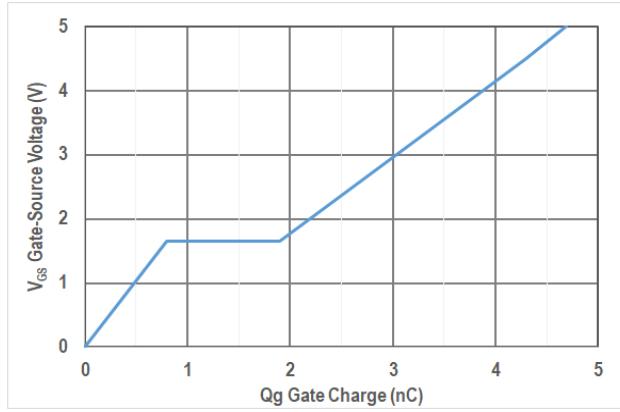


Figure4. Gate Charge

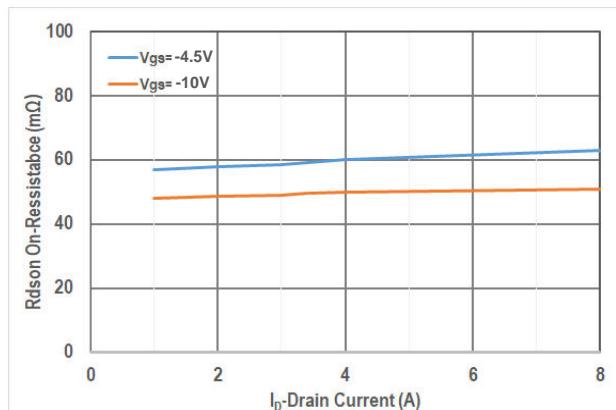


Figure5. Drain-Source on Resistance

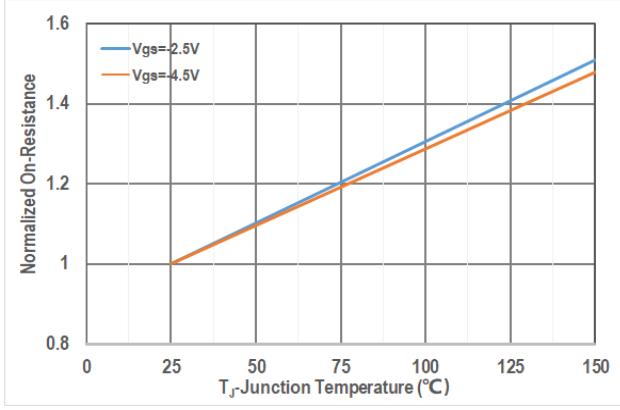


Figure6. Drain-Source on Resistance

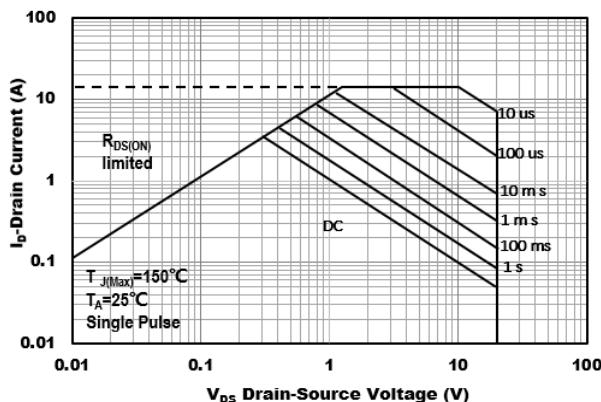


Figure7. Safe Operation Area

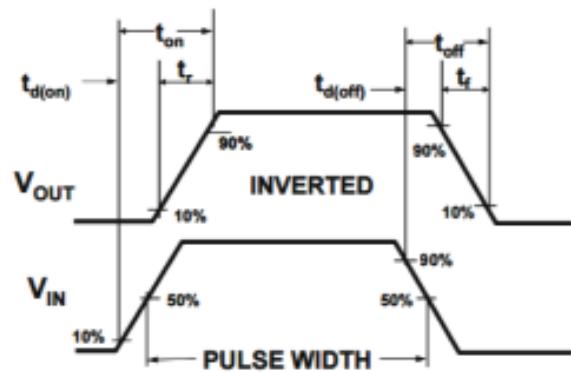
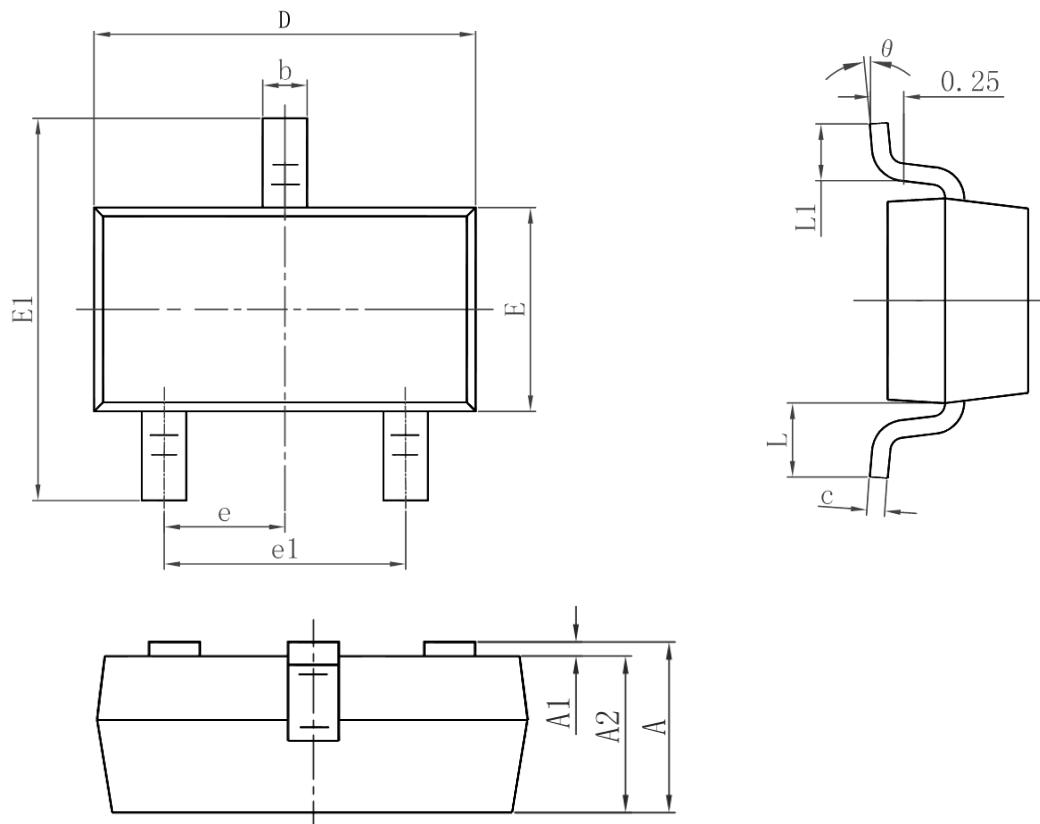


Figure8. Switching wave

## Package Information : SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	8°

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